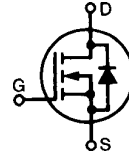


# HiPerFET™ Power MOSFETs Q-Class

## IXFJ 32N50Q

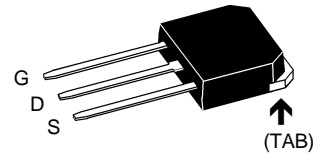
$V_{DSS} = 500 \text{ V}$   
 $I_{D(cont)} = 32 \text{ A}$   
 $R_{DS(on)} = 0.15 \text{ } \Omega$   
 $t_{rr} < 250 \text{ ns}$

N-Channel Enhancement Mode  
Avalanche Rated  
High dv/dt, Low  $t_{rr}$ , HDMOS™ Family



Preliminary data sheet

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	500	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	500	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	32	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	128	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	32	A
$E_{As}$	$T_C = 25^\circ\text{C}$	1.5	J
$E_{AR}$	$T_C = 25^\circ\text{C}$	45	mJ
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2 \text{ } \Omega$	5	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	360	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$



G = Gate, D = Drain,  
S = Source, TAB = Drain

### Features

- Low profile, high power package
- Long creep and strike distances
- Easy up-grade path for TO-220 designs
- Low  $R_{DS(on)}$ , low Qg process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance  
- easy to drive and to protect
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

### Advantages

- High power, low profile package
- Space savings
- High power density

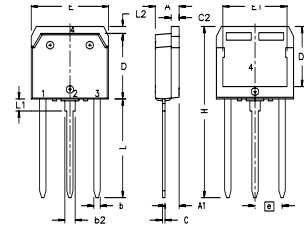
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ } \mu\text{A}$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	2		V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$ , $T_J = 125^\circ\text{C}$			100 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ Pulse test, $t \leq 300 \text{ } \mu\text{s}$ , duty cycle $d \leq 2 \%$			0.15 $\Omega$

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>g<sub>fs</sub></b>	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 0.5 I <sub>D25</sub> , pulse test	18	28	S
<b>C<sub>iss</sub></b>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz		3950	pF
<b>C<sub>oss</sub></b>			640	pF
<b>C<sub>rss</sub></b>			210	pF
<b>t<sub>d(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub> R <sub>G</sub> = 2 Ω (External)		35	ns
<b>t<sub>r</sub></b>			42	ns
<b>t<sub>d(off)</sub></b>			75	ns
<b>t<sub>f</sub></b>			20	ns
<b>Q<sub>g(on)</sub></b>	V <sub>GS</sub> = 10 V, V <sub>DS</sub> = 0.5 • V <sub>DSS</sub> , I <sub>D</sub> = 0.5 I <sub>D25</sub>		153	nC
<b>Q<sub>gs</sub></b>			26	nC
<b>Q<sub>gd</sub></b>			85	nC
<b>R<sub>thJC</sub></b>			0.35	K/W
<b>R<sub>thCK</sub></b>		0.25		K/W

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values		
		(T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
<b>I<sub>S</sub></b>	V <sub>GS</sub> = 0 V			32 A
<b>I<sub>SM</sub></b>	Repetitive; pulse width limited by T <sub>JM</sub>			128 A
<b>V<sub>SD</sub></b>	I <sub>F</sub> = I <sub>S</sub> , V <sub>GS</sub> = 0 V, Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.5 V
<b>t<sub>rr</sub></b>	I <sub>F</sub> = I <sub>S</sub> -di/dt = 100 A/μs, V <sub>R</sub> = 100 V			250 ns
<b>Q<sub>rr</sub></b>			0.75	μC
<b>I<sub>RM</sub></b>			7.5	A

### TO-268 Outline



All metal area are solder plated  
 1 - gate  
 2 - drain (collector)  
 3 - source (emitter)  
 4 - drain (collector)

Dim.	Inches		Millimeters	
	Min	Max	Min	Max
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	.040	.065
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	1.365	1.395	34.67	35.43
L	.780	.800	19.81	20.32
L1	.079	.091	2.00	2.30
L2	.039	.045	1.00	1.15

Figure 1. Output Characteristics at 25°C

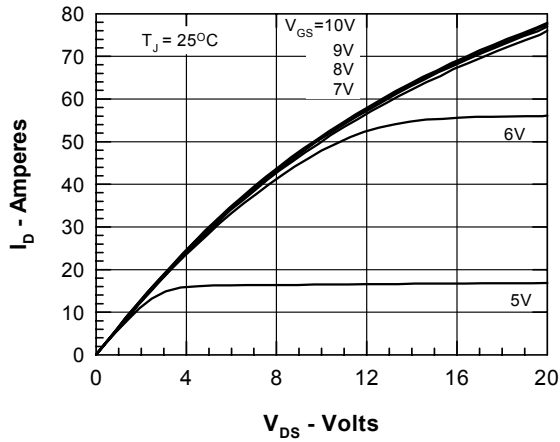


Figure 2. Output Characteristics at 125°C

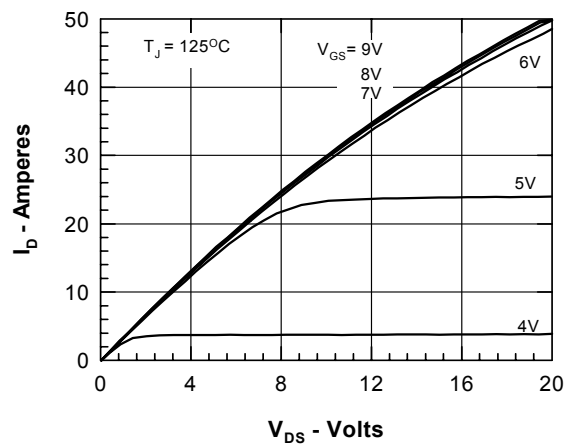


Figure 3.  $R_{DS(on)}$  normalized to 15A/25°C vs.  $I_D$

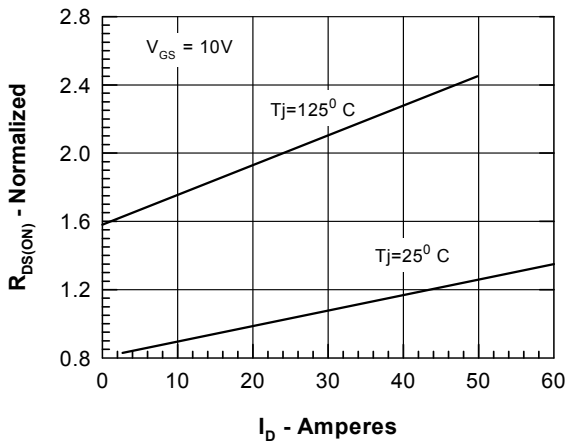


Figure 4.  $R_{DS(on)}$  normalized to 15A/25°C vs.  $T_J$

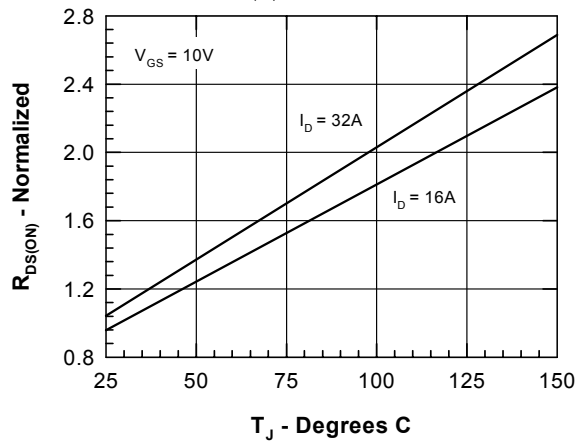


Figure 5. Drain Current vs. Case Temperature

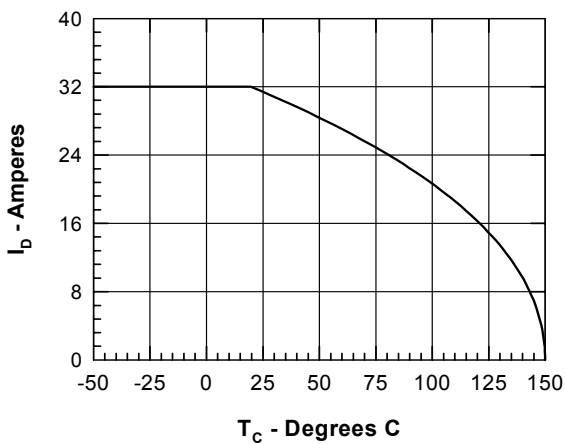


Figure 6. Admittance Curves

